

TO-92 Plastic-Encapsulate Transistors

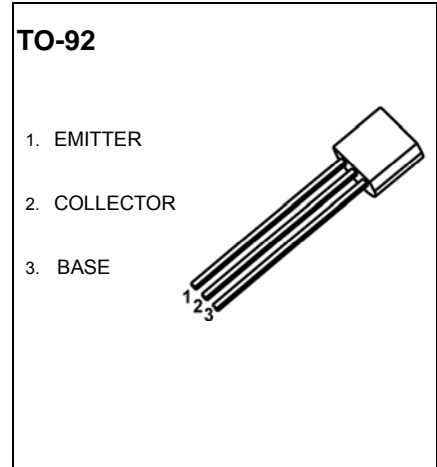
2SC388 TRANSISTOR (NPN)

FEATURES

- TV Final Pictureif Amplifier Applications

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Emitter Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current -Continuous	50	mA
P _C	Collector Power dissipation	300	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =5mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =3V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =12.5V, I _C =12.5mA	20		200	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =15mA, I _B =1.5mA			0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =15mA, I _B =1.5mA			1.2	V
Transition frequency	f _T	V _{CE} =12.5V, I _C =12.5mA	300			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	0.8		2	pF
Power Gain	G _{pe}	V _{CC} =12.5V, I _E =-12.5mA, f=45MHz	28		36	dB